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U.S. Department of Commerce, Patent and Trademark		Atty. Docket No.	Application No.
INFORMATION DISCLOSURE STATEMENT BY APPLICANT		SNDK.211US0 (formerly M-10311 US)	09793,370
		Applicants	101804,770
(Use several sheets if necessary)		Geoffrey Gongwer and Daniel Guterman	
		Filing Date	Group
		February 26, 2001 - March 19, 2004	2825

U.S. Patent Documents

*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
<i>John</i>	1	4,628,487	Dec. 9, 1986	Smayling	—	—	
<i>John</i>	2	5,422,842	Jun. 6, 1995	Cernea et al.	—	—	
<i>John</i>	3	5,557,567	Sep. 17, 1996	Bergemont et al.	—	—	
<i>John</i>	4	5,796,652	Aug. 18, 1998	Takeshima et al.	—	—	
<i>John</i>	5	6,014,330	Jan. 11, 2000	Endoh et al.	—	—	
<i>John</i>	6	6,134,148	Oct. 17, 2000	Kawahara et al.	—	—	
<i>John</i>	7	6,266,270 B1	Jul. 24, 2001	Nobukata	—	—	

U.S. Published Patent Application Documents

*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate

Foreign Patent Documents

							Translation	
		Document	Date	Country	Class	Subclass	Yes	No

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

<i>John</i>	8	Chi, Min-hwa et al., "Low-Voltage Multi-level Flash Memory: Determination of Minimum Spacing Between Multi-levels," Semiconductor Electronics, 1996, ICSE 1996 Proceedings, 1996 IEEE International Conference Penang, Malaysia, November 26, 1996, pages 1-5.
<i>John</i>	9	Chi, Min-hwa et al., "Multi-level Flash/EPROM Memories: New Self-convergent Programming Methods for Low-voltage Applications," Electron Devices Meeting, December 10, 1995, pp. 271-274.
<i>John</i>	10	Ohkawa, Masayoshi et al., "A 98mm ² 3.3V 64Mb Flash Memory with FN-NOR Type 4-level Cell," IEEE International Solid-State Circuits Conference, February 8, 1996, pp. 36-37 and 413.
<i>John</i>	11	International Search Report in counterpart PCT application PCT/US02/05265, Dec. 3, 2002, 5pages.

Examiner *John Melsaun* Date Considered 8/15/2004

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with your communication to applicant.

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U.S. Department of Commerce, Patent and Trademark Office		Atty Docket No.	Serial No.
		M-10311 US	09/793,370
INFORMATION DISCLOSURE STATEMENT BY APPLICANT		Applicants	10/804,770
(Use several sheets if necessary)		Gongwer et al.	
		Filing Date March 19, 2004	Group
		February 26, 2001	2825

U.S. Patent Documents

*Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
gfm	AA 5,220,531	6/15/93	Blyth et al.	365	189.07	
gfm	AB 5,623,436	4/22/97	Sowards et al.	365	45	
gfm	AC 5,677,869	10/14/97	Fazio et al.	365	185.03	
gfm	AD 5,729,489	3/17/98	Fazio et al.	365	185.03	
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gfm	AF 5,768,192	6/16/98	Eitan	365	185.24	
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Foreign Patent Documents

						Translation	
	Document	Date	Country	Class	Subclass	Yes	No
AN							
AO							
AP							

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

	AQ	
	AR	
	AS	

Examiner D. M. Melsaas

Date Considered 8/5/2004

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